

# FL6L5203

## Silicon P-channel MOS FET (FET) Silicon epitaxial planar type (SBD)

For DC-DC converter circuits

For switching circuits

### ■ Overview

FL6L5203 is P-channel type MOS FET with Schottky Barrier Diode in small size surface mounting package.

### ■ Features

- Low drive voltage: 2.5 V
- Low forward voltage  $V_F$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

### ■ Packaging

FL6L5203L Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
FET	Drain-source surrender voltage	$V_{DSS}$	-20	V
	Gate-source surrender voltage	$V_{GSS}$	$\pm 12$	V
	Drain current	$I_D$	-1.0	A
	Peak drain current	$I_{DP}$	-4.0	A
	Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
SBD	Reverse voltage	$V_R$	20	V
	Forward current (Average)	$I_{F(AV)}$	800	mA
	Junction temperature	$T_j$	125	$^\circ\text{C}$
Overall	Total power dissipation *	$P_D$	540	mW
	Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \*: Measuring on ceramic substrate at (40 mm × 38 mm × 0.2 mm)

Absolute maximum rating without heat sink for  $P_D$  is 150 mW

### ■ Package

#### • Code

WSSMini6-F1

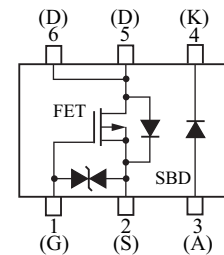
Package dimension clicks here.→

#### • Pin Name

1: Gate	4: Cathode
2: Source	5: Drain
3: Anode	6: Drain

### ■ Marking Symbol: Y3

### ■ Internal Connection



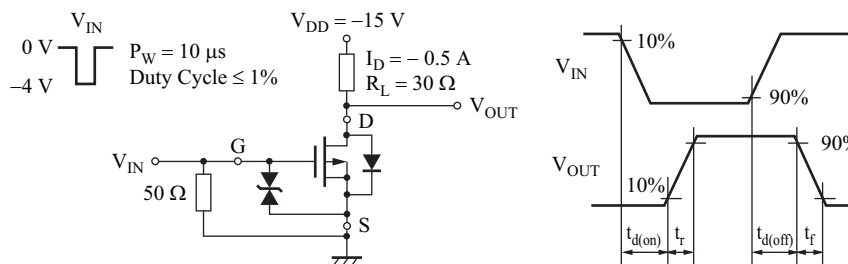
■ Electrical Characteristics  $T_a = 25^{\circ}\text{C} \pm 3^{\circ}\text{C}$

• FET

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Drain-source surrender voltage	$V_{DSS}$	$I_D = -1.0 \text{ mA}, V_{GS} = 0$	-20			V	
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0$			-1.0	$\mu\text{A}$	
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$			$\pm 10$	$\mu\text{A}$	
Gate threshold voltage	$V_{TH}$	$I_D = -1.0 \mu\text{A}, V_{DS} = -10 \text{ V}$	-0.45	-1.0	-1.5	V	
Drain-source ON resistance *1	$R_{DS(on)}$	$I_D = -0.5 \text{ mA}, V_{GS} = -4.0 \text{ V}$		300	420	$\mu\Omega$	
		$I_D = -0.5 \text{ mA}, V_{GS} = -2.5 \text{ V}$		420	560		
Forward transfer admittance *1	$ Y_{fs} $	$I_D = -0.5 \text{ mA}, V_{DS} = -10 \text{ V}, f = 1 \text{ MHz}$	1.0			S	
Short-circuit input capacitance (Common source)	$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		80		pF	
Short-circuit output capacitance (Common source)	$C_{oss}$				12		pF
Reverse transfer capacitance (Common source)	$C_{rss}$				12		pF
Turn-on delay time *2	$t_{d(on)}$	$V_{DD} = -15 \text{ V}, V_{GS} = 0 \text{ V to } -4 \text{ V}, I_D = -1.0 \text{ A}$		12		ns	
Rise time *2	$t_r$				6		ns
Turn-off delay time *2	$t_{d(off)}$	$V_{DD} = -15 \text{ V}, V_{GS} = -4 \text{ V to } 0 \text{ V}, I_D = -1.0 \text{ A}$		17		ns	
Fall time *2	$t_f$				10		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. \*1: Pulse measurement
- \*2: Test circuit



• SBD

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 800 \text{ mA}$			0.47	V
Reverse current	$I_R$	$V_R = 20 \text{ V}$			80	$\mu\text{A}$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

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